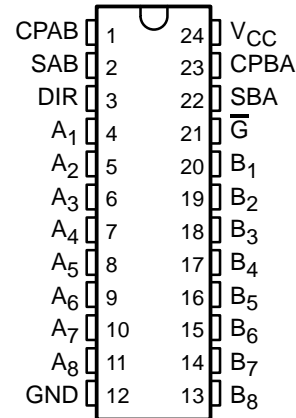- **Function, Pinout, and Drive Compatible With FCT and F Logic**
- **Reduced V_{OH} (Typically = 3.3 V) Versions of Equivalent FCT Functions**
- **Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Matched Rise and Fall Times**
- **Fully Compatible With TTL Input and Output Logic Levels**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**
- **Independent Register for A and B Buses**
- **CY54FCT646T**
  - **48-mA Output Sink Current**
  - **12-mA Output Source Current**
- **CY74FCT646T**
  - **64-mA Output Sink Current**
  - **32-mA Output Source Current**
- **3-State Outputs**

CY54FCT646T . . . D PACKAGE
CY74FCT646T . . . Q OR SO PACKAGE
(TOP VIEW)

CPAB	1	24	V_{CC}
SAB	2	23	CPBA
DIR	3	22	SBA
A_1	4	21	$\overline{G}$
A_2	5	20	B_1
A_3	6	19	B_2
A_4	7	18	B_3
A_5	8	17	B_4
A_6	9	16	B_5
A_7	10	15	B_6
A_8	11	14	B_7
GND	12	13	B_8

CY54FCT646T . . . L PACKAGE
(TOP VIEW)

Top pins (left to right): DIR, SAB, CPAB, NC, V_{CC}, CPBA, SBA (pins 4, 3, 2, 1, 28, 27, 26)

A_1	5	25	$\overline{G}$
A_2	6	24	B_1
$A3$	7	23	B_2
NC	8	22	NC
A_4	9	21	B_3
A_5	10	20	B_4
A_6	11	19	B_5

Bottom pins (left to right): A_7, A_8, GND, NC, B_8, B_7, B_6 (pins 12, 13, 14, 15, 16, 17, 18)

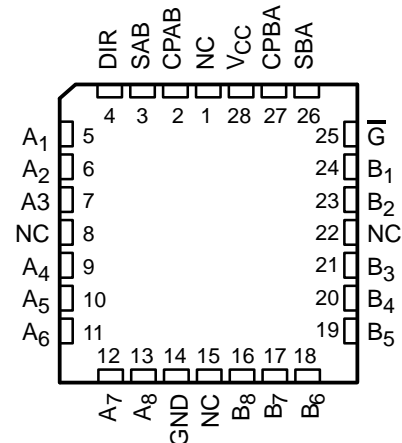NC – No internal connection

description

The 'FCT646T devices consist of a bus transceiver circuit with 3-state, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers as the appropriate clock pin goes to a high logic level. Output-enable ($\overline{G}$) and direction (DIR) inputs control the transceiver function. In the transceiver mode, data present at the high-impedance port can be stored in either the A or B register, or in both. Select controls (SAB, SBA) can multiplex stored and real-time (transparent mode) data. DIR determines which bus receives data when $\overline{G}$ is low. In the isolation mode ($\overline{G}$ is high), A data can be stored in the B register and/or B data can be stored in the A register.

These devices are fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TEXAS INSTRUMENTS

PIN DESCRIPTION

NAME	DESCRIPTION
A	Data register A inputs, data register B outputs
B	Data register B inputs, data register A outputs
CPAB, CPBA	Clock-pulse inputs
SAB, SBA	Output data-source-select inputs
DIR, $\overline{G}$	Output-enable inputs

ORDERING INFORMATION

T_A	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 85°C	QSOP – Q	Tape and reel	5.4	CY74FCT646CTQCT	FCT646C
	SOIC – SO	Tube	5.4	CY74FCT646CTSOC	FCT646C
		Tape and reel	5.4	CY74FCT646CTSOCT	
	QSOP – Q	Tape and reel	6.3	CY74FCT646ATQCT	FCT646A
	SOIC – SO	Tube	6.3	CY74FCT646ATSOC	FCT646A
		Tape and reel	6.3	CY74FCT646ATSOCT	
	QSOP – Q	Tape and reel	9	CY74FCT646TQCT	FCT646
	SOIC – SO	Tube	9	CY74FCT646TSOC	FCT646
		Tape and reel	9	CY74FCT646TSOCT	
−55°C to 125°C	LCC – L	Tube	6	CY54FCT646CTLMB	
	CDIP – D	Tube	7.7	CY54FCT646ATDMB	
	LCC – L	Tube	7.7	CY54FCT646ATLMB	
		Tube	11	CY54FCT646TLMB	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

INPUTS						DATA I/O‡		OPERATION OR FUNCTION
$\overline{G}$	DIR	CPAB	CPBA	SAB	SBA	A_1–A_8	B_1–B_8	
H	X	H or L	H or L	X	X	Input	Input	Isolation
H	X	↑	↑	X	X	Input	Input	Store A and B data
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

H = High logic level, L = Low logic level, ↑ = Low-to-high transition, X = Don't care
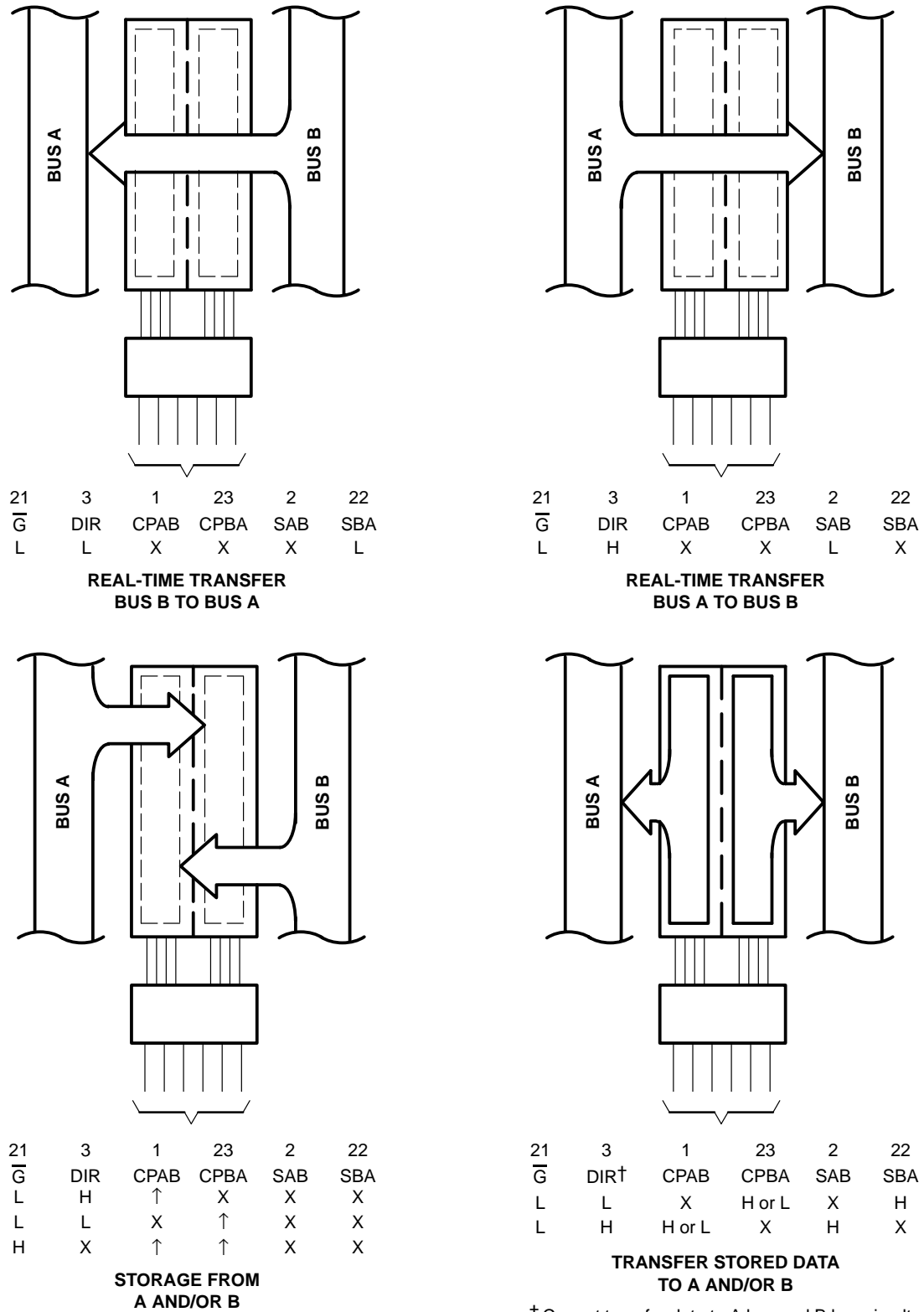
‡ The data output functions can be enabled or disabled by various signals at the $\overline{G}$ or DIR inputs. Data input functions always are enabled, i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.

21	3	1	23	2	22
$\overline{G}$	DIR	CPAB	CPBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A

21	3	1	23	2	22
$\overline{G}$	DIR	CPAB	CPBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B

21	3	1	23	2	22
$\overline{G}$	DIR	CPAB	CPBA	SAB	SBA
L	H	↑	X	X	X
L	L	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A AND/OR B

21	3	1	23	2	22
$\overline{G}$	DIR[†]	CPAB	CPBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

[†] Cannot transfer data to A bus and B bus simultaneously.

Figure 1. Bus-Management Functions

logic diagram (positive logic)

One of Eight Channels

To Seven Other Channels
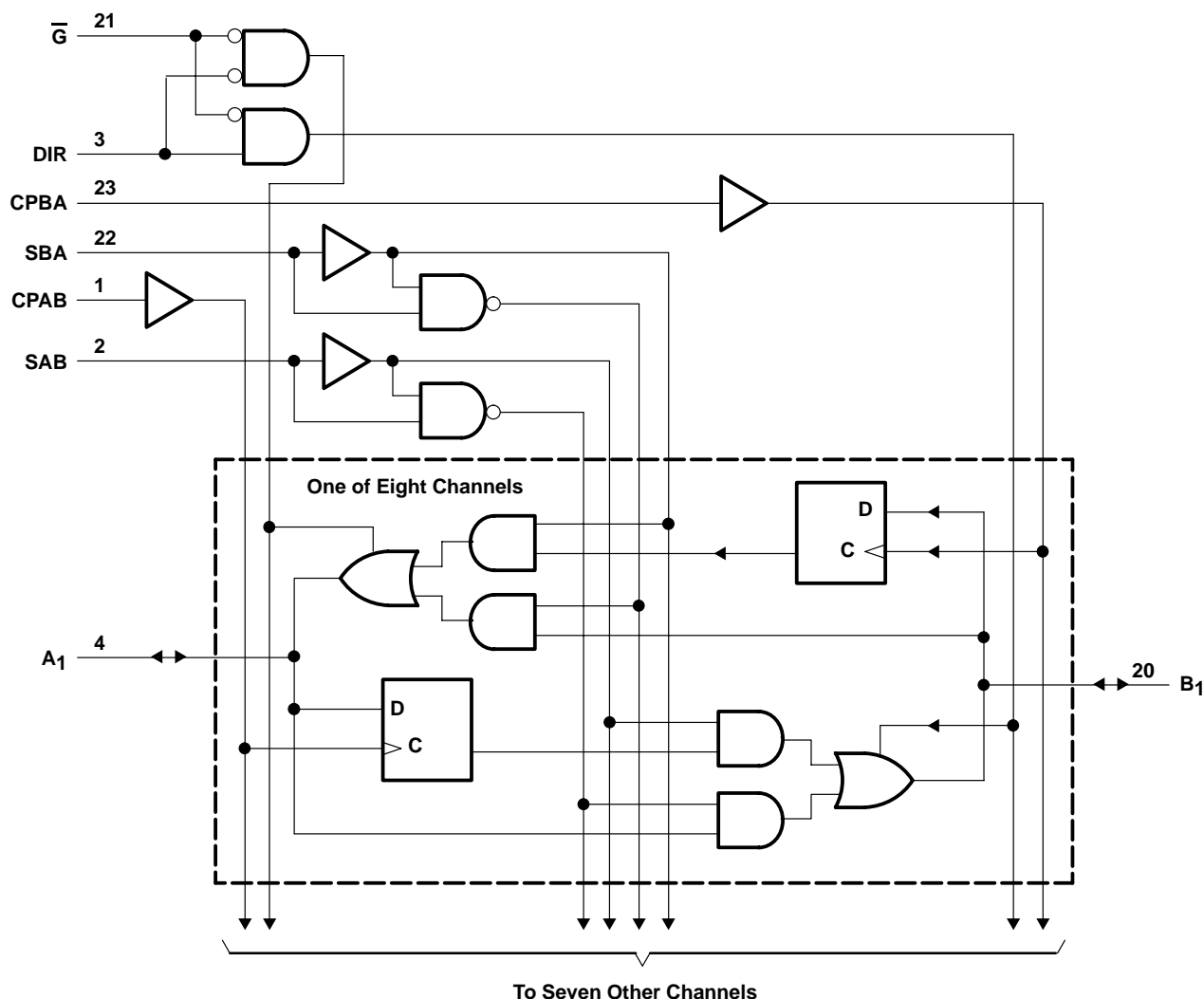
Pin numbers shown are for the Q and SO packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range to ground potential	–0.5 V to 7 V
DC input voltage range	–0.5 V to 7 V
DC output voltage range	–0.5 V to 7 V
DC output current (maximum sink current/pin)	120 mA
Package thermal impedance, θ_{JA} (see Note 1): Q package	61°C/W
SO package	46°C/W
Ambient temperature range with power applied, T_A	–65°C to 135°C
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51-7.

TEXAS INSTRUMENTS

recommended operating conditions (see Note 2)

		CY54FCT646T			CY74FCT646T			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	4.5	5	5.5	4.75	5	5.25	V
V_{IH}	High-level input voltage	2			2			V
V_{IL}	Low-level input voltage			0.8			0.8	V
I_{OH}	High-level output current			–12			–32	mA
I_{OL}	Low-level output current			48			64	mA
T_A	Operating free-air temperature	–55		125	–40		85	°C

NOTE 2: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		CY54FCT646T			CY74FCT646T			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	$V_{CC} = 4.5$ V,	$I_{IN} = -18$ mA		−0.7	−1.2				V
	$V_{CC} = 4.75$ V,	$I_{IN} = -18$ mA					−0.7	−1.2	
V_{OH}	$V_{CC} = 4.5$ V,	$I_{OH} = -12$ mA	2.4	3.3					V
	$V_{CC} = 4.75$ V	$I_{OH} = -32$ mA				2			
		$I_{OH} = -15$ mA				2.4	3.3		
V_{OL}	$V_{CC} = 4.5$ V,	$I_{OL} = 48$ mA		0.3	0.55				V
	$V_{CC} = 4.75$ V,	$I_{OL} = 64$ mA					0.3	0.55	
V_{hys}	All inputs			0.2			0.2		V
I_I	$V_{CC} = 5.5$ V,	$V_{IN} = V_{CC}$			5				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = V_{CC}$						5	
I_{IH}	$V_{CC} = 5.5$ V,	$V_{IN} = 2.7$ V			±1				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = 2.7$ V						±1	
I_{IL}	$V_{CC} = 5.5$ V,	$V_{IN} = 0.5$ V			±1				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = 0.5$ V						±1	
I_{OZH}	$V_{CC} = 5.5$ V,	$V_{OUT} = 2.7$ V			10				µA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 2.7$ V						10	
I_{OZL}	$V_{CC} = 5.5$ V,	$V_{OUT} = 0.5$ V			−10				µA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 0.5$ V						−10	
$I_{OS}‡$	$V_{CC} = 5.5$ V,	$V_{OUT} = 0$ V	−60	−120	−225				mA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 0$ V				−60	−120	−225	
I_{off}	$V_{CC} = 0$ V,	$V_{OUT} = 4.5$ V			±1			±1	µA
I_{CC}	$V_{CC} = 5.5$ V,	$V_{IN} \leq 0.2$ V, $\quad V_{IN} \geq V_{CC} - 0.2$ V		0.1	0.2				mA
	$V_{CC} = 5.25$ V,	$V_{IN} \leq 0.2$ V, $\quad V_{IN} \geq V_{CC} - 0.2$ V					0.1	0.2	
ΔI_{CC}	$V_{CC} = 5.5$ V, $V_{IN} = 3.4$ V§, $f_1 = 0$, Outputs open			0.5	2				mA
	$V_{CC} = 5.25$ V, $V_{IN} = 3.4$ V§, $f_1 = 0$, Outputs open						0.5	2	
$I_{CCD}¶$	$V_{CC} = 5.5$ V, One input switching at 50% duty cycle, Outputs open, $\overline{G}$ = DIR = GND, SAB = $\overline{SBA}$ = GND, $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V			0.06	0.12				mA/MHz
	$V_{CC} = 5.25$ V, One input switching at 50% duty cycle, Outputs open, $\overline{G}$ = DIR = GND, SAB = $\overline{SBA}$ = GND, $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V						0.06	0.12	

† Typical values are at $V_{CC} = 5$ V, $T_A = 25°C$.

‡ Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

§ Per TTL-driven input ($V_{IN} = 3.4$ V); all other inputs at V_{CC} or GND

¶ This parameter is derived for use in total power-supply calculations.

TEXAS
INSTRUMENTS

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS			CY54FCT646T			CY74FCT646T			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
I_C#	$V_{CC} = 5.5$ V, $f_0 = 10$ MHz, Outputs open, $\overline{G} = DIR = GND$, $SAB = \overline{SBA} = GND$	One bit switching at $f_1 = 5$ MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V		0.7	1.4				mA
			$V_{IN} = 3.4$ V or GND		1.2	3.4				
		Eight bits switching at $f_1 = 5$ MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V		2.8	5.6‖				
			$V_{IN} = 3.4$ V or GND		5.1	14.6‖				
	$V_{CC} = 5.25$ V, $f_0 = 10$ MHz, Outputs open, $\overline{G} = DIR = GND$, $SAB = \overline{SBA} = GND$	One bit switching at $f_1 = 5$ MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V					0.7	1.4	mA
			$V_{IN} = 3.4$ V or GND					1.2	3.4	
		Eight bits switching at $f_1 = 5$ MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V					2.8	5.6‖	
			$V_{IN} = 3.4$ V or GND					5.1	14.6‖	
C_i					6	10		6	10	pF
C_o					8	12		8	12	pF

I_C $\quad= I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD}(f_0/2 + f_1 \times N_1)$
  Where:
  I_C $\quad$ = Total supply current
  I_{CC} $\quad$ = Power-supply current with CMOS input levels
  ΔI_{CC} = Power-supply current for a TTL high input ($V_{IN} = 3.4$ V)
  D_H $\quad$ = Duty cycle for TTL inputs high
  N_T $\quad$ = Number of TTL inputs at D_H
  I_{CCD} = Dynamic current caused by an input transition pair (HLH or LHL)
  f_0 $\quad$ = Clock frequency for registered devices, otherwise zero
  f_1 $\quad$ = Input signal frequency
  N_1 $\quad$ = Number of inputs changing at f_1
  All currents are in milliamperes and all frequencies are in megahertz.
‖ Values for these conditions are examples of the I_{CC} formula.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		CY54FCT646T		CY54FCT646AT		CY54FCT646CT		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	6		5		5		ns
t_{su}	Setup time, data before CPAB↑ or CPBA↑	4.5		2		2		ns
t_h	Hold time, data after CPAB↑ or CPBA↑	2		1.5		1.5		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		CY74FCT646T		CY74FCT646AT		CY74FCT646CT		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	6		5		5		ns
t_{su}	Setup time, data before CPAB↑ or CPBA↑	4		2		2		ns
t_h	Hold time, data after CPAB↑ or CPBA↑	2		1.5		1.5		ns

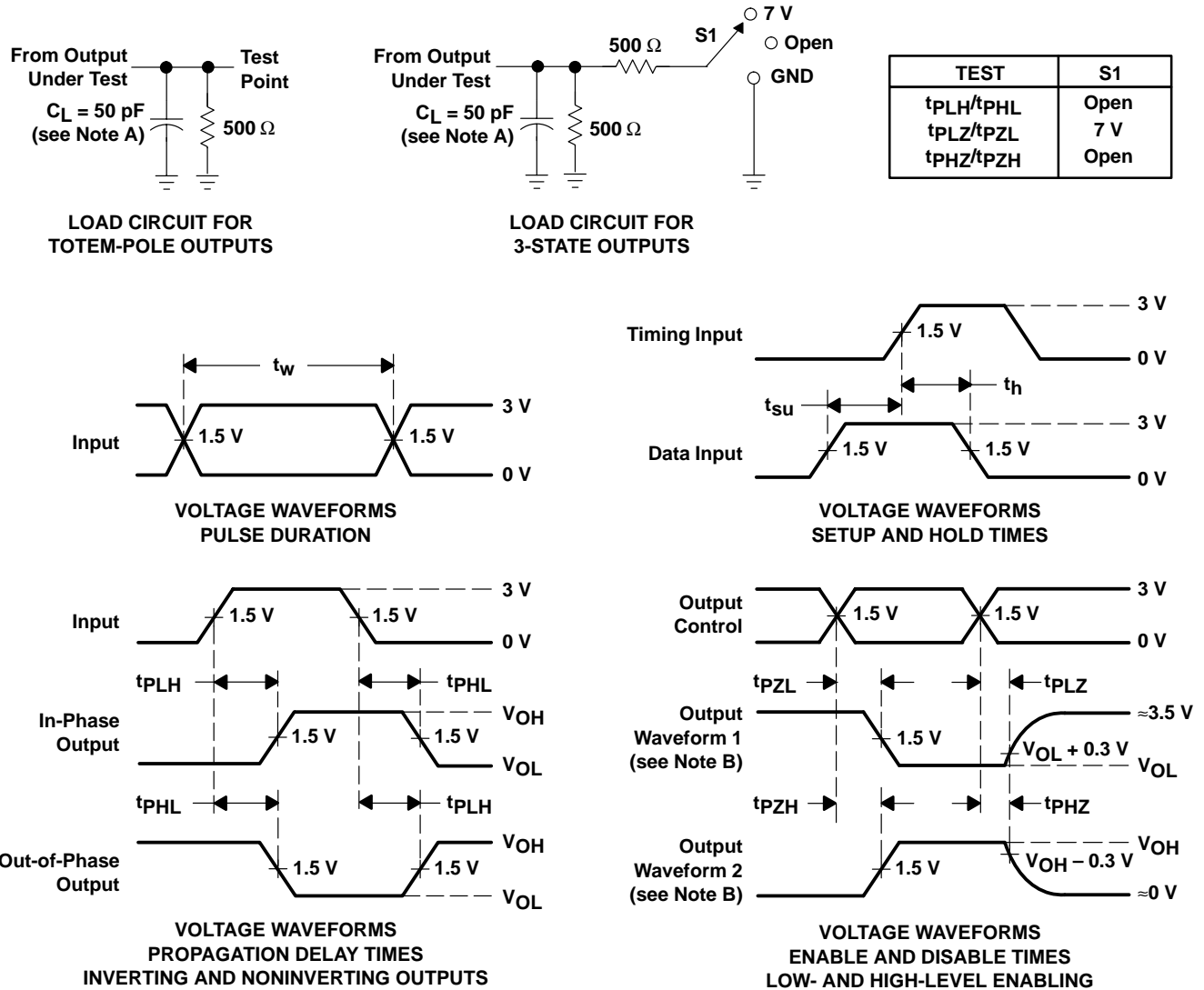**switching characteristics over operating free-air temperature range (see Figure 2)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CY54FCT646T		CY54FCT646AT		CY54FCT646CT		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	2	11	2	7.7	1.5	6	ns
t_{PHL}			2	11	2	7.7	1.5	6	
t_{PZH}	DIR	A or B	2	15	2	10.5	1.5	8.9	ns
t_{PZL}			2	15	2	10.5	1.5	8.9	
t_{PHZ}	$\overline{G}$ and DIR	A or B	2	11	2	7.7	1.5	7.7	ns
t_{PLZ}			2	11	2	7.7	1.5	7.7	
t_{PLH}	CPAB or CPBA	A or B	2	10	2	7	1.5	6.3	ns
t_{PHL}			2	10	2	7	1.5	6.3	
t_{PLH}	SBA or SAB	A or B	2	12	2	8.4	1.5	7	ns
t_{PHL}			2	12	2	8.4	1.5	7	

switching characteristics over operating free-air temperature range (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CY74FCT646T		CY74FCT646AT		CY74FCT646CT		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.5	9	1.5	6.3	1.5	5.4	ns
t_{PHL}			1.5	9	1.5	6.3	1.5	5.4	
t_{PZH}	DIR	A or B	1.5	14	1.5	9.8	1.5	7.8	ns
t_{PZL}			1.5	14	1.5	9.8	1.5	7.8	
t_{PHZ}	$\overline{G}$ and DIR	A or B	1.5	9	1.5	6.3	1.5	6.3	ns
t_{PLZ}			1.5	9	1.5	6.3	1.5	6.3	
t_{PLH}	CPAB or CPBA	A or B	1.5	9	1.5	6.3	1.5	5.7	ns
t_{PHL}			1.5	9	1.5	6.3	1.5	5.7	
t_{PLH}	SBA or SAB	A or B	1.5	11	1.5	7.7	1.5	6.2	ns
t_{PHL}			1.5	11	1.5	7.7	1.5	6.2	

PARAMETER MEASUREMENT INFORMATION

From Output Under Test

C_L = 50 pF
(see Note A)

Test Point

500 Ω

**LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS**

From Output Under Test

C_L = 50 pF
(see Note A)

500 Ω

500 Ω

S1

○ 7 V

○ Open

○ GND

**LOAD CIRCUIT FOR
3-STATE OUTPUTS**

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

Input

t_w

1.5 V   1.5 V

3 V

0 V

**VOLTAGE WAVEFORMS
PULSE DURATION**

Timing Input

1.5 V

3 V

0 V

t_{su} t_h

Data Input

1.5 V   1.5 V

3 V

0 V

**VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES**

Input

1.5 V   1.5 V

3 V

0 V

t_{PLH} t_{PHL}

In-Phase Output

1.5 V   1.5 V

V_{OH}

V_{OL}

t_{PHL} t_{PLH}

Out-of-Phase Output

1.5 V   1.5 V

V_{OH}

V_{OL}

**VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS**

Output Control

1.5 V   1.5 V

3 V

0 V

t_{PZL} t_{PLZ}

**Output Waveform 1
(see Note B)**

1.5 V

V_{OL} + 0.3 V

≈3.5 V

V_{OL}

t_{PZH} t_{PHZ}

**Output Waveform 2
(see Note B)**

1.5 V

V_{OH} – 0.3 V

V_{OH}

≈0 V

**VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING**

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. The outputs are measured one at a time with one input transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable part number (1)	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
5962-9222301M3A	Active	Production	LCCC (FK) | 28	42 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222301M3A
5962-9222303M3A	Active	Production	LCCC (FK) | 28	42 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222303M3A CY54FCT 646ATLMB
5962-9222303MLA	Active	Production	CDIP (JT) | 24	15 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222303MLA CY54FCT646ATDMB
5962-9222305M3A	Active	Production	LCCC (FK) | 28	42 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222305M3A CY54FCT 646CTLMB
CY54FCT646ATDMB	Active	Production	CDIP (JT) | 24	15 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222303MLA CY54FCT646ATDMB
CY54FCT646ATLMB	Active	Production	LCCC (FK) | 28	42 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222303M3A CY54FCT 646ATLMB
CY54FCT646CTLMB	Active	Production	LCCC (FK) | 28	42 | TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9222305M3A CY54FCT 646CTLMB
CY74FCT646ATQCT	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT646A
CY74FCT646ATQCT.B	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT646A
CY74FCT646ATSOC	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646A
CY74FCT646ATSOC.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646A
CY74FCT646ATSOCT	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646A
CY74FCT646ATSOCT.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646A
CY74FCT646CTSOC	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646C
CY74FCT646CTSOC.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646C

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CY74FCT646TSOC	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646
CY74FCT646TSOC.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646
CY74FCT646TSOCT	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646
CY74FCT646TSOCT.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT646

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT646ATQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT646ATSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CY74FCT646TSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS
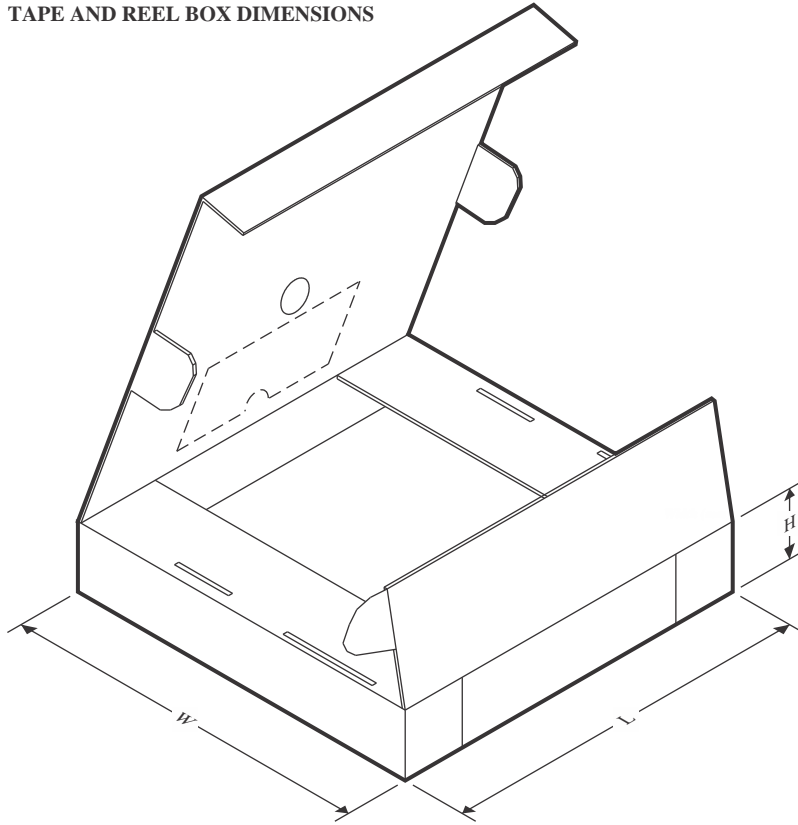
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT646ATQCT	SSOP	DBQ	24	2500	353.0	353.0	32.0
CY74FCT646ATSOCT	SOIC	DW	24	2000	350.0	350.0	43.0
CY74FCT646TSOCT	SOIC	DW	24	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

TUBE

T - Tube height

L - Tube length

W - Tube width

B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CY74FCT646ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT646ATSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT646CTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT646CTSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT646TSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT646TSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

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